Molecular Beam Epitaxy Grown Cr$_2$Te$_3$ Thin Films with Tunable Curie Temperatures

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**ABSTRACT**: Materials with perpendicular magnetic anisotropy (PMA) effect with high Curie temperature is essential in applications. Cr$_2$Te$_3$ is a material that demonstrates PMA effect but with a relatively low Curie temperature of about 180 K. In this work, Cr$_2$Te$_3$ thin films with Curie temperature ranging from 165 K to 295 K were successfully grown on Al$_2$O$_3$ by the molecular beam epitaxy (MBE) technique. To study the physical origin of the improved Curie temperature, structural analysis, magneto-transport and magnetic characterizations were conducted and analyzed in detail. In particular, the n-type feature of these thin films shows that they are an electron–enriched material. Ferromagnetic (FM) ordering and Anti Ferromagnetic (AFM) ordering competition were systematically investigated by magnetization characterizations. A
phenomenological model based on the degree of coupling between FM and AFM ordering was proposed to explain the observed Curie temperature enhancement in our samples. These findings indicate that the Curie temperature of Cr$_2$Te$_3$ thin films can be tuned and our material could act as a novel magnetic material with potential for various magnetic applications.

INTRODUCTION

Recently, chromium telluride compounds have attracted much interest due to their variable magnetic properties and compatible structures for realizing spintronic and magnetic memory devices based on chalcogenide compounds. Chromium telluride has a large family of compounds in the bulk state. All these compounds are of Hexagonal structure and ferromagnetic ordering at stable states with a wide range of Curie temperature from 170 K to 340 K, depending sensitively on the atomic ratio between Cr and Te. In the bulk state, the Chromium Telluride with Cr/Te ratio around 1:1 has the highest Curie temperature around 340 K [1-3], while the other phases of chromium telluride with Cr vacancy around 0.1–0.33 have Curie temperature between 150 K-340 K. Not only the Curie temperature, the magnetic anisotropy of the chromium telluride compounds also depends on the stoichiometric ratio as well as the lattice structure intimately. Recently, many efforts had been made on the growth of chromium telluride thin films on semiconducting substrates. For example, structural and magnetic properties of hexagonal Cr$_2$Te$_3$ films grown on CdTe (001) with Curie temperature of 175 K has been studied by Ken Kanazawa et al [4]. A perpendicular magnetic anisotropy (PMA) and spin-glass-like behavior of hexagonal Cr$_2$Te$_3$ grown on sapphire (0001) and Si (111) substrates with Curie temperature of about 180 K were studied systematically [5]. The thin Cr$_2$Te$_3$ ferromagnetic metallic film was used in a field effect capacitor (FEC) structure at
temperature of 175 K [6]. Saito et al. have studied tunneling magnetoresistance (TMR) in the magnetic tunneling junctions (MTJs) with Cr$_{1-\delta}$Te being one of the electrodes around 170 K [7]. All above researches already show that the hexagonal phase Cr$_{1-\delta}$Te thin films possess promising potentials for the application in the spintronic and spin transfer torque device development. However, the Curie temperature of the epitaxially grown Chromium Telluride thin films is still desired to be further improved for fabricating reliable devices working at room temperature.

Even though the $T_c$ for bulk hexagonal phase Cr$_{1-\delta}$Te can reach as high as 340 K when Cr/Te ratio reaches 1:1, their easy axis is orthogonal to the c-axis, which made it unlikely to be used in devices [3, 8]. Several works have been reported for the growth of Zinc blende CrTe on GaAs (001) substrate with ZnTe or CdTe buffer layer [6, 9-11]. However, the fragile nature of the Zinc blend structure still prevents its practical application. Hereby, we report that Cr$_2$Te$_3$ thin films with a stable NiAs-type hexagonal structure grown on Al$_2$O$_3$ (0001) substrates by the MBE technique enjoy high Curie temperature. Careful studies on the strain and lattice constant show that the Curie temperature is sensitively determined by the (001) plane spacing of Cr$_2$Te$_3$ thin films. To the best of our knowledge, our work achieved the highest Curie temperature for NiAs-type Chromium Telluride thin films grown by epitaxial schemes, which will pave the way for the fabrication of chalcogenide based spintronic devices working at near ambient conditions.

**EXPERIMENTAL**

[001] oriented Cr$_2$Te$_3$ thin films were grown on epi-ready Al$_2$O$_3$ (0001) substrates (HF-Kejing, China) in a customized MBE system with base ultrahigh vacuum better than $1 \times 10^{-10}$ Torr. Before the growth, Al$_2$O$_3$ (0001) substrates were annealed at 600 °C for 15 minutes to degas. Chromium (99.999% Goodfellow UK)
and tellurium (99.999% Goodfellow UK) were evaporated by two Knudsen-type effusion cells for providing independent fluxes, respectively, and co-deposited on the substrate at 370 °C. The flux ratio between Chromium and Tellurium atom was determined to be around 1:7. Ex-situ thickness characterization is done by atomic force microscopy and XRR, indicating that the growth rate was about 1nm/min. To investigate the property of Cr$_2$Te$_3$ grown on Al$_2$O$_3$ substrates systematically, several Cr$_2$Te$_3$ samples with different thicknesses named as sample #1 (15 nm), #2 (30 nm), #3 (45 nm) and #4 (300 nm) were grown.

A 15 keV in-situ reflection high-energy electron diffraction (RHEED) is used to monitor the growth. A Rigaku High-resolution X-ray diffractometer (XRD), Talos transmission electron microscope (TEM) coupled with energy dispersive x-ray spectrometer (EDX) and an FEI Titan Spherical aberration corrected transmission electron microscope (STEM) were employed to study the lattice structure and atomic ratio of the as-grown chromium telluride thin films. The magnetic properties were studied using Quantum Design superconducting quantum interference diffractometer (SQUID). Transport properties are measured using an Oxford Physical Property Measurement System (PPMS).

RESULTS AND DISCUSSIONS

Figure 1 displays the RHEED patterns observed for the growth of a typical Cr$_2$Te$_3$ thin film sample. Figure 1(a) & (b) are the RHEED patterns of a cleaned Al$_2$O$_3$ (0001) surface along the [10-10] and [11-20] electron beam incidence, respectively, after a pre-heat treatment was conducted. Kikuchi lines can be clearly seen in these patterns, indicating a clean and smooth surface morphology of the substrate was achieved. Corresponding RHEED patterns observed after the growth of a Cr$_2$Te$_3$ thin film are shown in
Figure 1(c) & (d). Half-order reconstruction lines are seen in both patterns, reflecting that the as-grown Cr$_2$Te$_3$ thin film has a high crystalline quality. The long streaky patterns were maintained during the entire Cr$_2$Te$_3$ growth process, suggesting that its growth was via a two-dimensional growth mode with an atomically flat surface.

Figure 2(a) shows the XRD profile of sample #2 as a typical result for the Cr$_2$Te$_3$ thin film samples presented in this work. The layer peaks (004) and (008) in Figure 2(a) match well with the hexagonal structure of Cr$_2$Te$_3$ oriented along the [001] direction, while the (006) peak is from the Al$_2$O$_3$ substrate. The derived c-lattice parameter is 12.985 Å for Al$_2$O$_3$, same as the standardized database in Springer Materials [12]. The c-lattice parameter of the Cr$_2$Te$_3$ layer of sample #2 is 12.304 Å. The thickness dependence of the c-lattice parameter of the layer peak was further studied among the four Cr$_2$Te$_3$ samples. Figure 2(b) shows the XRD (008) peaks of these samples (samples #1 – #4) with their c-lattice parameters determined to be 12.255 Å, 12.304 Å, 12.309 Å and 12.327 Å, indicating that the c-lattice parameter increases with sample thickness and the increasing rate becomes slower when the Cr$_2$Te$_3$ thickness reaches about 30 nm. It is worth to note that all these values are larger than the reported c-lattice parameter of bulk hexagonal Cr$_2$Te$_3$, which is 12.07 Å [13]. We believe that this difference may be caused by unexpected Al incorporation in the layers through diffusion from the Al$_2$O$_3$ substrate, which will be addressed later. On the other hand, the observed increase of the c-lattice parameter with increasing sample thickness for our Cr$_2$Te$_3$ thin films may be attributed to the lattice relaxation effect. This is because the bulk values of the lattice constants in the ab plane or along the c-lattice plane of our Cr$_2$Te$_3$ thin films are smaller than the bulk values of the Al$_2$O$_3$ substrate, thus one should expect a thin Cr$_2$Te$_3$ layer grown on this substrate will be stretched out along the
ab plane but compressed along the c-axis, as the thickness increases, the c-lattice spacing will gradually increase to its ultimate bulk value, even though still larger than the conventional bulk lattice caused by the Al incorporation.

The magnetization versus temperature (M–T) curve from 2–320 K under an applied field of $H = 1000$ Oe perpendicular to the surface and resistance versus temperature (R–T) curve from 2–300K for sample #2 are shown in Figure 3(a). Both the M–T and R–T curves show a typical behavior of ferromagnetism around their para–ferro transition upon cooling. Curie temperature is obtained by performing the first derivation of these curves. As shown in Figure 3(b), the peak and valley at 244 K in the derivative curves indicate the Curie temperature at which magnetization and resistance change abruptly. We have carried out similar studies for the other samples. Figure 3(c) displays the M-T curves for all four samples, in which, sample #4 was under a magnetic field of 50 Oe to show a clearer low-temperature behavior, which will be addressed later. These M-T curves show that a tuning of Curie temperature from 165 K to 295 K can be achieved by varying their thicknesses that somehow might be related to the c-lattice parameter as illustrated in Figure 2(b). In the following paragraphs, we will present the results of further structural, magnetic and magneto-transport measurements to address the underlying mechanism of the observed tunability of the Curie temperature of our Cr$_2$Te$_3$ samples.

Figure 4 displays the typical cross-sectional TEM images near the interface between Cr$_2$Te$_3$ and Al$_2$O$_3$ viewing along the [-1 -2 0] direction of Al$_2$O$_3$. Two types of domains with different orientations of Cr$_2$Te$_3$, one along the [1 1 0] direction (Figure 4(a)) and the other along the [-1 -2 0] direction (Figure 4(c)) are found. As estimated from all the available TEM images, we found that more domains that atoms arranged
like Figure 4(c) were found than those arranged like Figure 4(a). It should be noted that an amorphous layer with thickness ~ 2nm can be seen at the interface between the Cr₂Te₃ layer and the Al₂O₃ substrate for both domain types. Structural simulations for both TEM images are given accordingly in Figure 4(b) and (d).

Chemical composition characterization of the Cr₂Te₃ layer in the area that is far away from the interface is performed by EDX installed in the STEM. Figure 4(e) displays the STEM image from a domain like the one shown in Figure 4(c), which is used for this characterization. The resulted mapping for Cr, Te and Al are shown in Figure 4(f), (g) and (h) respectively. The distribution of Te element shown in Figure 4(g) is in good consistency with the TEM graph shown in Figure 4(e). Cr atoms which cannot be observed in the TEM graph due to its small atomic radius, can be observed in the EDX mapping. The EDX mapping result of Cr atoms (Figure 4(f)) shows that Cr atoms which are represented by relative bright blue dots are interspersed between Te atoms roughly consistent with the structure as shown in Figure 4(d). Besides Cr and Te elements, small amount of Al is identified. The effect of Al contamination will be discussed later.

To determine the composition of the amorphous layer shown in Figure 4, we performed EDX mapping using the EDX facility installed in the TEM equipment. The TEM graph taken in HADDF mode is shown in Figure 5(a). Here, we use a standard analyzing technique in EDX, which is called EDX line profile analyzing. In Figure 5(a), we draw two green lines across the interface (amorphous layer) between the Cr₂Te₃ layer and the Al₂O₃ substrate. Figure 5(b) and (c) are the enlarged corresponding distribution results of the Al and O atomic fraction along these two lines. In these figures, the x-axis shows the distance from the starting points of the green lines, while the vertical black lines represent the approximate positions of the amorphous layer shown in Figure 5(a). In Figure 5(b), which is drawn from the Al₂O₃ layer to the Cr₂Te₃,
layer, when the atomic fraction of O element becomes zero at about 65 nm, the atomic fraction of Al hits the highest value. Similarly, in Figure 5(c), which is drawn from the Cr$_2$Te$_3$ layer to the Al$_2$O$_3$ layer, when the atomic fraction of Al reaches a peak value at about 78.5 nm, which means the ending of the Cr$_2$Te$_3$ layer, the atomic fraction of O is still zero. These results show that the amorphous layer is likely a pure Al layer and the thickness is about 2 nm. Similar observation for the growth of GaN on Al$_2$O$_3$ has been reported by Wenliang Wang et al [14]. They named it as nitridation effect of Al$_2$O$_3$. In our Cr$_2$Te$_3$ sample, the tellurium-rich environment may cause the top few layers of the Al$_2$O$_3$ substrate to suffer from oxygen deficiency. However, more work is needed to verify this speculation.

Now let us revisit the observed Al contamination in our Cr$_2$Te$_3$ layers and see how it may affect the electrical transport of these layers. To our best knowledge, the conduction type of all Cr$_2$Te$_3$ bulk or thin film materials reported previously is p-type [1]. Cr$_2$Te$_3$ samples grown on ZnSe in our group also show p-type feature [15]. To investigate the effect of Al contamination, a six-terminal Hall bar device was fabricated on a small piece of sample #2, as shown in Figure 6(a) for performing magneto-transport measurements. The width and length of the device are 1000 μm and 500 μm respectively. Its Hall resistance was derived from the voltage along the XY direction with a current of 50μA flowing along the XX direction as specified in Figure 6(a). The results of Hall effect measurements performed on sample #2 are shown in Figure 6(b) with $R_{xy}(H)$ curves having been offset vertically for clarity. At 280 K, the measured Hall resistivity is linearly dependent on H field, which is a typical feature of ordinary Hall effect (OHE). However, below Curie temperature (244 K), a clear hysteresis behavior is observed, which is an indicator of the anomalous Hall effect (AHE) that arises from the ferromagnetic ordering. At low temperature, the
hysteresis loop narrows and vanishes at 100 K. As temperature decreases further, $R_{xy}$ reverses its sign comparing with $R_{xy}$ measured at temperature above 100 K. The observed temperature dependent AHE is related to several transport mechanisms of the charge carriers and the details of our analysis will be reported elsewhere [16]. Here, we would like to focus on the observation that the overall Hall resistance decreases with magnetic field, as shown in Figure 6(b), which indicates that sample #2 is n-type in conduction type. The carrier concentration is derived by linearly fitting the Hall resistance $R_{xy}$ to magnetic field at large magnetic-field values. The carrier concentration of sample #2 is estimated to be about $10^{21}$ cm$^{-3}$ using this approach. We believed that the observed Al contamination causes our Cr$_2$Te$_3$ thin films grown on Al$_2$O$_3$ substrate to be n-type by contributing free electrons. It has been reported that the change of orbital ordering induced by electrons can enhance the Curie temperature of manganites thin films [17]. The improved Curie temperature of our Cr$_2$Te$_3$ thin films may partially be attributed to the same mechanism.

The magnetic hysteresis loop measured for sample #2 is shown in Figure 7. The measured magnetization curve (M–H curve) with the applied magnetic field perpendicular to the sample surface shows a square shaped loop with coercive force around 0.25 T and shifts into a round shape when the applied magnetic field is parallel to the sample surface, indicating a strong spin frustration in ab plane for preventing the full polarization. The observed contrast of magnetization behaviors along different orientations indicates a perpendicular magnetic anisotropy in the as–grown Cr$_2$Te$_3$ thin film, consistent with previous reports on the easy axis of Cr$_2$Te$_3$ compound$^5$. However, the hysteresis loop is not saturated with magnetic field up to 1.5 T, offering the evidence of the existence of AFM order in this thin film. What’s more, a small step-like kink feature around the zero–field region is found in the hysteresis loop for $H_\perp$ plane. This step-like kink is
usually observed in magnetic systems with complicated magnetic ordering, such as spin-glass [18], ferromagnetic/antiferromagnetic co-existence and nanoparticle magnetic system [19-21]. The following discussion pursuing the possible cause of the observed step-like kink will be limited to the first two possible mechanisms, since the third one is inadequate for an epitaxial thin film like our Cr$_2$Te$_3$ thin films presented here. More evidences will be given in the following magnetic studies to understand the magnetic structure of our Cr$_2$Te$_3$ thin films.

To study the physical origin of the step-like kink shown in Figure 7, zero field cooled (ZFC) and field cooled (FC) M–T curves are measured simultaneously. Magnetic remanence ($M_r$) measurements are conducted to study if our material is a spin glass or spin cluster. Figure 8(a) shows the ZFC and FC curves of sample #2 with a magnetic field of 100 Oe, 500 Oe, 1000 Oe and 2000 Oe respectively perpendicular to the sample surface. FC curves were measured while cooling down from 320 K. ZFC curves were measured while warming up with the same magnetic field used for measuring FC curves after cooling from 320 K without magnetic field. The obtained FC magnetization curves correspond to a typical magnetization behavior of ferromagnetism. The ZFC curves display an increase of magnetization when warming up from 2 K for all curves, followed by a decrease of magnetization after a characteristic temperature, and eventually merge with the FC magnetization curves at a blocking temperature $T_b$. With increasing magnetic field, the blocking temperature decreases. The temperature dependent magnetization behavior further confirm that the step-like kink observed in M-H loop is induced by the possible complex magnetic ordering existing in the Cr$_2$Te$_3$ thin films. Regarding the two possible mechanisms for the observed magnetization behaviors described above, a typical behavior of spin-glass or spin-cluster is that the magnetic moments will decay
after withdrawing external magnetic field [22]. Magnetic remanence ($M_r$) of sample #2 was conducted at 2.1 K after applying a 2 T magnetic field perpendicular to the sample surface and withdrawing back to zero quickly, as shown in Figure 8(b). The out of plane $M_r$ stays at a constant value with measuring time at least up to 60 mins, which is a signature of ferromagnetism. Thus, the occurrence of discrepancy in ZFC and FC M–T curves of sample #2 is not a signature of pure spin-glass or spin cluster, leaving the antiferromagnetic/ferromagnetic coexistence remaining as the only valid mechanism.

In fact, it is widely considered that in the Cr fully occupied layer of chromium telluride, moments are ferromagnetically ordered [1], while in the Cr vacancy layer, the moments are antiferromagnetically ordered [23-26]. Based on the above magnetic experiments, we believe that the small kinks in the M–H curves of our samples are a consequence of the coexistence of FM ordering and AFM ordering. The FM ordering in the Cr fully occupied layer and AFM ordering in the Cr vacancy layer will couple with each other and the strength could be sensitively affected by the c-lattice parameter. From a close inspection of the M-T curve of sample #4 (which is 300 nm thick, the thickest layer among the four samples), as shown in Figure 3(c), a drop of its moment is found at 110K. In contrast, the FC curve measured with a magnetic field of 100 Oe for sample #2, as shown in Figure 8(a), shows no drop of moment. Although the FC measurement of sample #2 with magnetic field of 50 Oe was not conducted because its signal is expected to be too weak to be detected at such a low applied field, we can speculate that the drop of moment observed in sample #4 might be originated from the weaken coupling between AFM ordering and FM ordering in its $Cr_2Te_3$ layer. Further evidence of this claim comes from the magnetic hysteresis loops of $Cr_2Te_3$ samples with different thicknesses as shown in Figure 8(c). The magnetic moments are normalized to -1 to 1 and offset vertically.
for clarity. The coercive field decreases as thickness of Cr$_2$Te$_3$ layer increases, providing further evidence for the existence of different magnetic regimes. With increasing thin film thickness, the distance between the atomic layers of Cr$_2$Te$_3$ gets larger. Considering that a small AFM ordering exists in the Cr vacancy layer, with increasing distance between the atomic layers, the coupling between FM ordering and AFM ordering gets smaller. Thus, it is easier for moments ferromagnetically ordered to be aligned to the external magnetic field. What’s more, the step-like kinks which is induced by the coupling between FM ordering and AFM ordering also becomes less obvious. The above observations indicate that our observed improvement of the Curie temperature of the Cr$_2$Te$_3$ layer as its c-lattice parameter increases can be attributed to the weaken FM and AFM coupling. In fact, previous high-pressure studies on Cr$_2$Te$_3$ samples grown by others indicate that the Curie temperature decreases with the contraction of c-axis [27, 28]. In our work, the observed enhancement of T$_C$ in our samples can be attributed to the same mechanism with an opposite direction that the c-axis is extended.

CONCLUSIONS

MBE-grown hexagonal Cr$_2$Te$_3$ thin films grown on Al$_2$O$_3$ substrates were found to enjoy high Curie temperature. In-situ long streaky reflection high energy electron diffraction patterns observed in the Cr$_2$Te$_3$ thin films indicate that they were grown with atomically flat surface with high crystalline quality. It was found that a 2 nm amorphous layer of Al exists at the interface between Cr$_2$Te$_3$ and Al$_2$O$_3$ and a small amount of Al contamination is incorporated into the Cr$_2$Te$_3$ layer, which induces the n-type conduction type of our samples in contrast to the p-type signature observed for Cr$_2$Te$_3$ samples as reported by others previously. A phenomenological model for the coupling between FM ordering and AFM ordering that exists
in our Cr$_2$Te$_3$ thin films is proposed based on the results of the magnetic characterizations performed on them. The phenomenon that Curie temperature increases as the c-lattice parameter increases can be explained using our proposed phenomenological model.

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**ACKNOWLEDGMENTS**

This work was supported by the National Natural Science Foundation of China (No. 11774143), the National Key Research and Development Program of China (No. 2018YFA0307100, No. 2016YFA0301703), the Natural Science Foundation of Guangdong Province (No. 2015A030313840, No. 2017A030313033), the State Key Laboratory of Low-Dimensional Quantum Physics (No. KF201602), Technology and Innovation Commission of Shen-zhen Municipality (KQJSCX20170727090712763, ZDSYS20170303165926217, and JCYJ20170412152334605).

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Verlag Berlin Heidelberg & Material Phases Data System (MPDS), Switzerland & National Institute for Materials Science (NIMS), Japan.


Figure 1. RHEED patterns observed for the growth of a typical Cr$_2$Te$_3$ thin film. (a) & (b) RHEED patterns from a clean Al$_2$O$_3$ (0001) surface with the incident electron beam along the [10-10] and [11-20] orientations of Al$_2$O$_3$, respectively; (c) & (d) Corresponding RHEED patterns from the Cr$_2$Te$_3$ surface along the same orientations.
Figure 2. X-ray diffraction (XRD) profiles of Cr$_2$Te$_3$ thin films. (a) XRD profile of sample #2; (b) XRD profiles of the (008) peak of Cr$_2$Te$_3$ thin films with increasing thicknesses
Figure 3. The magnetization characterization of sample #1−#4. (a) R–T and M–T curves of sample #2; (b) First derivation of R–T and M–T curves of sample #2; (c) M–T curves measured for samples #1−#4 with magnetic field perpendicular to the surface.
Figure 4. TEM images and EDX mapping results of a Cr$_2$Te$_3$ sample. (a) & (c) The cross-section TEM graph of the interface, (b) & (d) show the structure simulation corresponding to (a) & (c) respectively (e): an area in (c) used for EDX mapping. (f) & (g) & (h) show EDX mapping of Cr, Te, and Al element respectively for the area shown in (e).
Figure 5. (a) TEM picture used for EDX mapping; (b) EDX line profile of the left green line in (a); (c) EDX line profile of the right green line in (a). The black lines in (b) and (c) mark the approximate location of the center of the amorphous layer.
Figure 6. Results of Hall effect measurements performed on sample #2. (a) Schematic drawing of the Hall measurement device; (b) temperature dependent $R_{xx}$ vs magnetic field strength from 2K to 280 K of sample #2.
Figure 7. MH curves of sample #2 with magnetic field perpendicular and parallel to the surface respectively measured at 2.1 K. The arrows indicate the small step-like kinks.
Figure 8. Results of various magnetic moment measurements performed on Cr$_2$Te$_3$ samples. (a) ZFC and FC curves of sample #2 with magnetic field perpendicular to the surface; (b) Magnetic remanence of sample #2 measured at 2.1 K with magnetic field perpendicular to the sample surface; (c) magnetic hysteresis loops measured for sample #1 – #4 with magnetic field perpendicular to the surface.